WPM3401

Single P-Channel, -30V, -4.6A, Power MOSFET

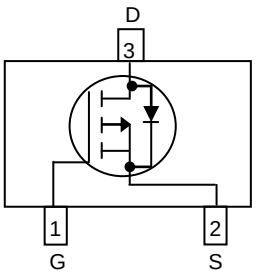
www.sh-willsemi.com

V_{DS} (V)	Max R_{DS} (on) (mΩ)
-30	53@ V_{GS}=−10V
	56@ V_{GS}=−4.5V

SOT-23-3L

Descriptions

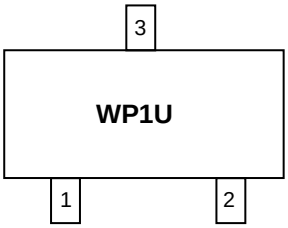
The WPM3401 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high-side switching.



Pin configuration (Top view)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Small package SOT-23-3L



WP1= Specific Device Code
U = Date Code

Marking

Applications

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch

Order information

Device	Package	Shipping
WPM3401-3/TR	SOT-23-3L	3000/Reel&Tape

Absolute Maximum ratings

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	-30		V
Gate-Source Voltage		V_{GS}	±12		
Continuous Drain Current [a]	T_A=25°C	I_D	-5.5	-4.6	A
	T_A=70°C		-4.4	-3.6	
Maximum Power Dissipation [a]	T_A=25°C	P_D	1.7	1.3	W
	T_A=70°C		1.1	0.8	
Continuous Drain Current [b]	T_A=25°C	I_D	-5.0	-4.2	A
	T_A=70°C		-4.0	-3.4	
Maximum Power Dissipation [b]	T_A=25°C	P_D	1.4	1.0	W
	T_A=70°C		0.9	0.6	
Pulsed Drain Current [c]		I_{DM}	-20		A
Operating Junction Temperature		T_J	150		°C
Lead Temperature		T_L	260		°C
Storage Temperature Range		T_{stg}	-55 to 150		°C

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance [a]	t ≤ 10 s	$R_{\theta JA}$	70	90	°C/W
	Steady State		95	125	
Junction-to-Ambient Thermal Resistance [b]	t ≤ 10 s	$R_{\theta JA}$	85	105	
	Steady State		120	150	
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	40	60	

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR-4 board using minimum pad size, 1oz copper

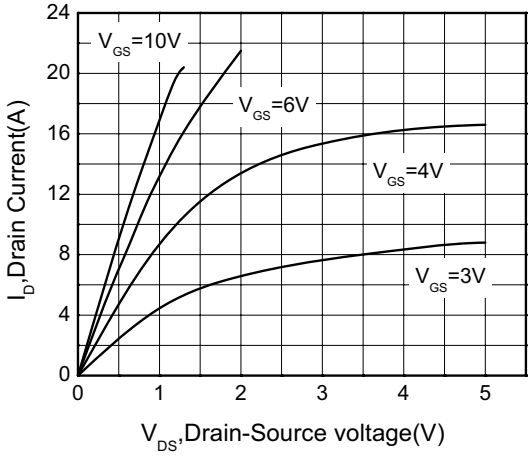
c Pulse width<380μs, Duty Cycle<2%

d Maximum junction temperature T_J=150°C.

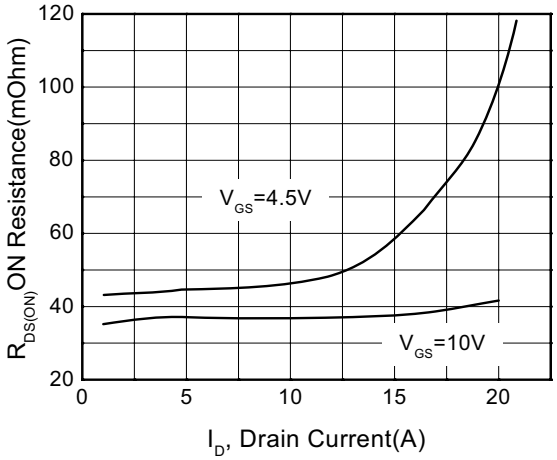
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0 V, I_D = -250uA	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24V, V_{GS} = 0V			-1	uA
		V_{DS} = -24V, V_{GS} = 0V,T_J=85 °C			-5	
Gate-to-source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±12V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = -250uA	-0.5	-1.0	-1.5	V
On State Drain Current (Pulse) [b, c]	$I_{D(on)}$	V_{DS} =-5 V, V_{GS} = -4.5V	-10			A
Drain-to-source On-resistance [b, c]	$R_{DS(on)}$	V_{GS} = -10V, I_D = -4.3A		38	53	mΩ
		V_{GS} = -4.5V, I_D = -3.5A		43	56	
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = -1.0A		-0.75	-1.5	V
Forward Transconductance	G_{FS}	V_{DS} = -15V, I_D = -4.3A		13		s
CAPACITANCES, CHARGES						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = -15V		1250		pF
Output Capacitance	C_{OSS}			106		
Reverse Transfer Capacitance	C_{RSS}			90		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = -10 V, V_{DD} = -10 V, I_D = -4.3A		24.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.3		
Gate-to-Source Charge	Q_{GS}			2.2		
Gate-to-Drain Charge	Q_{GD}			1.8		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V_{GEN} = -10 V,V_{DD} = -15 V, I_D=-1.0A,R_G=6Ω, R_L=15Ω		10		ns
Rise Time	tr			18		
Turn-Off Delay Time	td(OFF)			60		
Fall Time	tf			9		

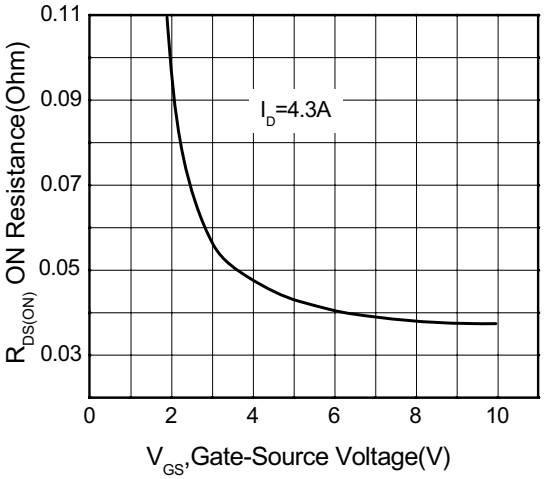
Typical Characteristics (Ta=25°C, unless otherwise noted)



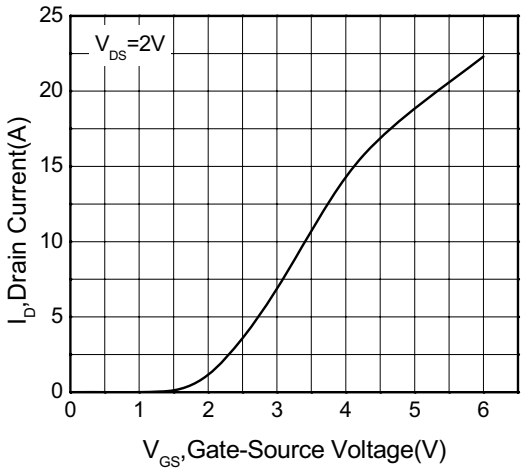
Drain Current VS Drain-Source voltage



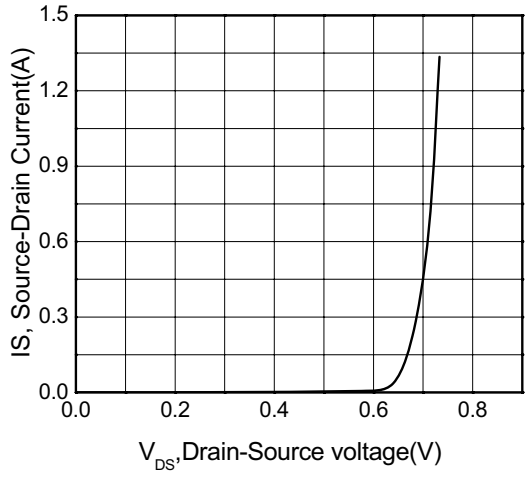
Drain Current vs ON Resistance



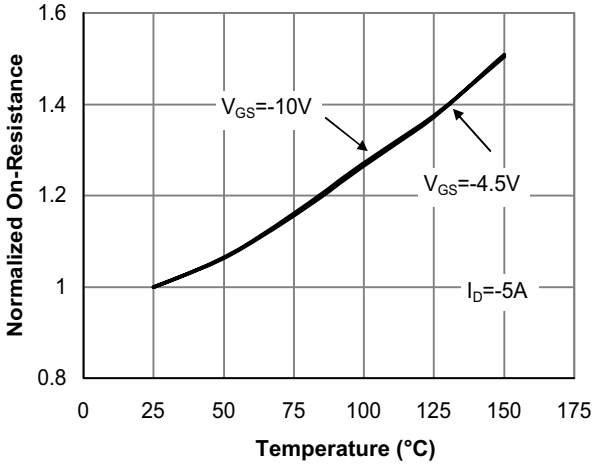
Gate-Source Voltage vs ON Resistance



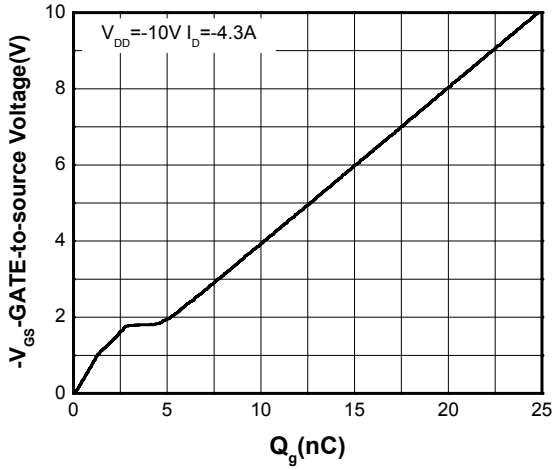
Drain Current VS Gate-Source Voltage



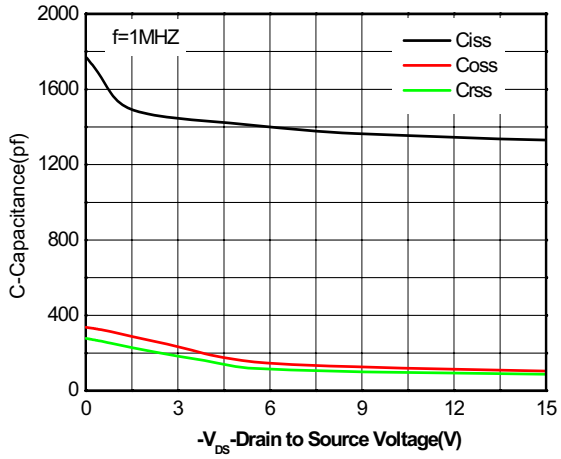
Drain Current VS Source-Drain Current



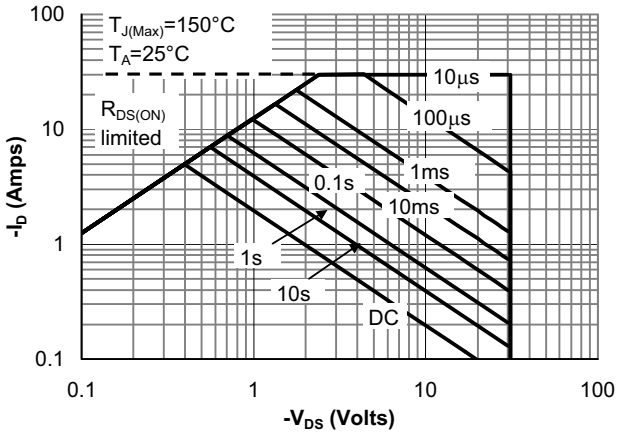
On-Resistance vs. Junction



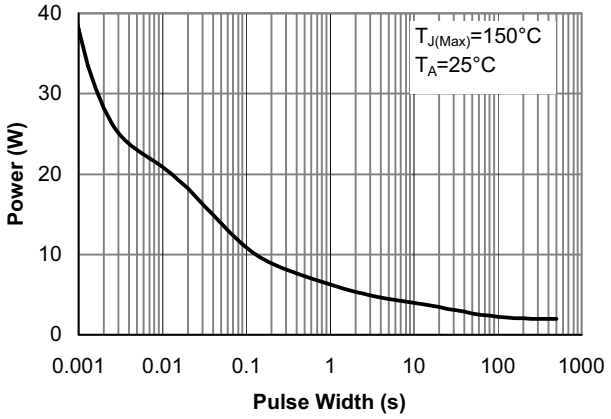
Gate Charge Characteristics



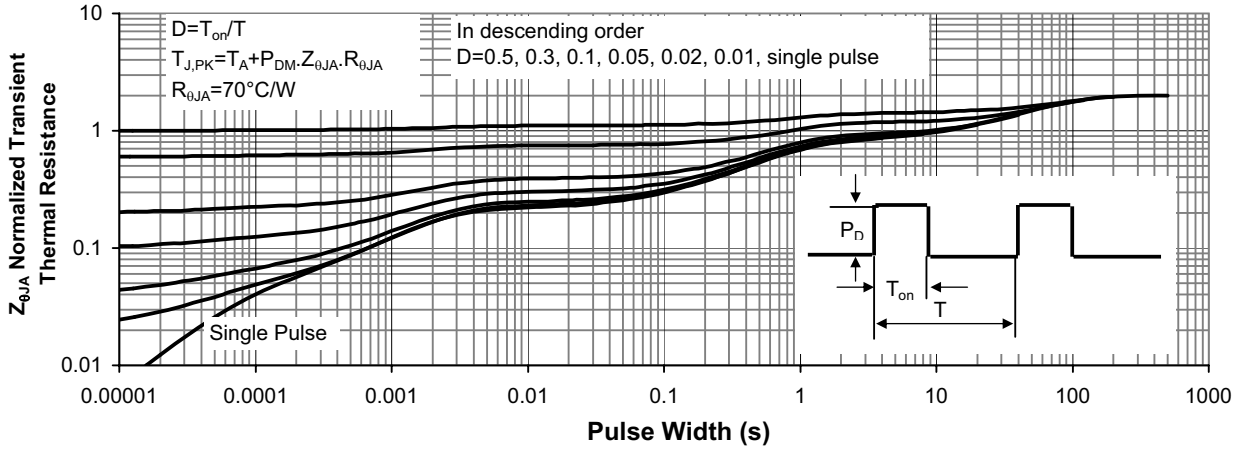
Capacitance Characteristics



Maximum Forward Biased Safe Operating Area (Note E)



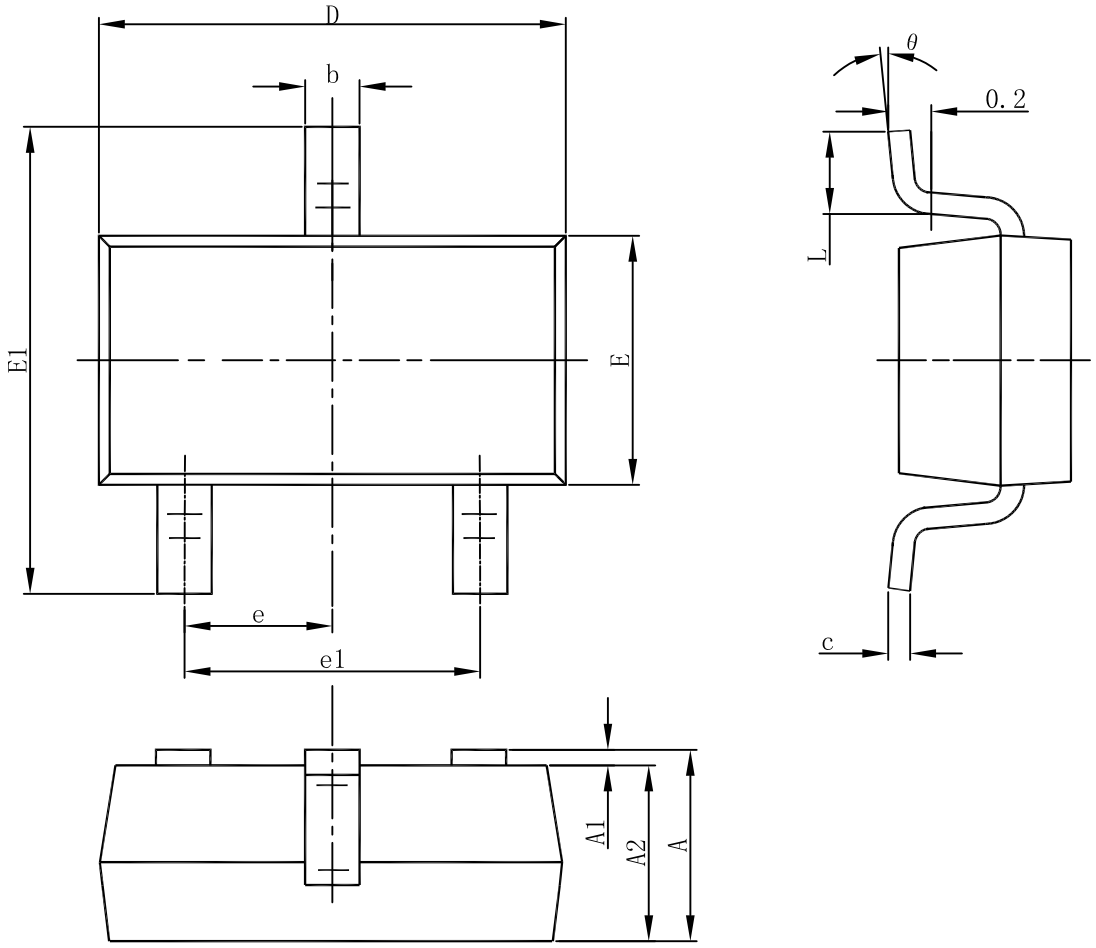
Single Pulse Power Rating Junction-to-Ambient (Note E)



Normalized Maximum Transient Thermal Impedance

Package outline dimensions

SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°